

NONVOLATILE MEMORY AND
METHOD OF MAKING SAME

Abstract of the Disclosure

- A method of discharging a charge storage location of a transistor of a non-volatile
- 5 memory includes applying first and second voltages to a control gate and a well region, respectively, of the transistor. The first voltage is applied to the control gate of the transistor, wherein the control gate has at least a portion located adjacent to a select gate of the transistor. The transistor includes a charge storage location having nanoclusters disposed within dielectric material of a structure of the transistor located below the control gate.
- 10 Lastly, a second voltage is applied to the well region located below the control gate. Applying the first voltage and the second voltage generates a voltage differential across the structure for discharging electrons from the nanoclusters of the charge storage location.